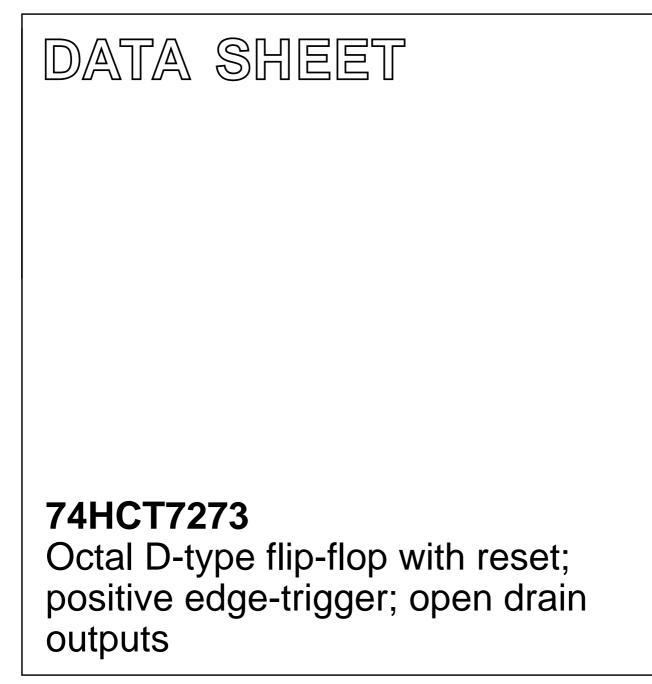
INTEGRATED CIRCUITS



Product specification File under Integrated Circuits, IC06 1999 Oct 01



FEATURES

- ESD protection: HBM EIA/JESD22-A114-A Exceeds 2000 V MM EIA/JESD22-A115-A Exceeds 200 V
- Ideal buffer for MOS microprocessor or memory
- Eight positive edge-triggered D-type flip-flops
- Common clock and master reset
- Output capability: standard (open drain)
- I_{CC} category: MSI.

DESCRIPTION

The 74HCT7273 is a high-speed SI-gate CMOS device and is pin compatible with Low power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard no 7A.

The 74HCT7273 has eight edge-triggered D-type flip-flops with individual D inputs and Q outputs. The common Clock (CP) and Master Reset ($\overline{\text{MR}}$) inputs load and reset (clear) all flip-flops simultaneously.

The state of each D input, one set-up time before the LOW-to-HIGH clock transition, is transferred to the corresponding output (Q_n) of the flip-flop.

A LOW level on the $\overline{\text{MR}}$ input forces all outputs LOW, independently of the clock or data inputs.

The device is useful for applications requiring true outputs only and clock and master reset inputs that are common to all storage elements.

The 74HCT7273 has open-drain N-outputs, which are clamped by a diode connected to V_{CC} . When a HIGH is clocked in the flip-flop, the output comes in the high-impedance OFF-state. The output may now be pulled to any voltage between GND and V_{Omax} . This allows the device to be used as a LOW-to-HIGH or HIGH-to-LOW level shifter. For digital operation and OR-tied output applications, the device must have a pull-up resistor to establish a logic HIGH level.

QUICK REFERENCE DATA

Ground = 0 V; $T_{amb} = 25 \text{ °C}$; $t_r = t_f = 6.0 \text{ ns.}$

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PZL} /t _{PLZ}	propagation delay	$C_L = 50 \text{ pF}; V_{CC} = 4.5 \text{ V}$		
	CP to Q _n		16	ns
	MR to Q _n		23	ns
f _{max}	maximum clock frequency		56	MHz
CI	input capacitance		3.5	pF
C _{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz}; \text{ notes } 1 \text{ and } 2$	37	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o) + \sum (V_0^2/R_L) \times duty$ factor LOW where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 $\Sigma (C_L \times V_{CC}^2 \times f_o) = sum of outputs;$

 C_L = output load capacitance in pF;

 R_L = pull-up resistor in M Ω ;

 V_{CC} = supply voltage in Volts.

2. The condition is $V_I = GND$ to $V_{CC} - 1.5$ V.

74HCT7273

FUNCTION TABLE

See note 1.

OPERATING MODES		INPUTS	OUTPUTS		
OPERATING MODES	MR	СР	D _n	Q _n	
Reset (clear)	L	Х	Х	L	
Load '1'	Н	↑	h	Z	
Load '0'	Н	1		L	

Note

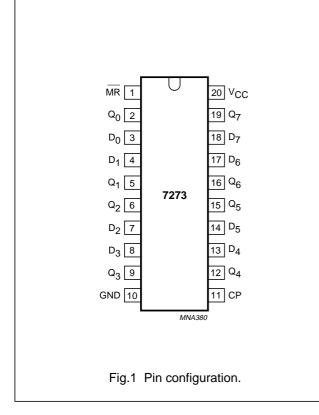
- 1. H = HIGH voltage level;
 - h = HIGH voltage level one set-up time prior to the LOW-to-HIGH CP transition;
 - L = LOW voltage level.
 - I = LOW voltage level one set-up time prior to the LOW-to-HIGH CP transition;
 - Z = high-impedance OFF-state;
 - X = don't care;
 - \uparrow = LOW-to-HIGH CP transition.

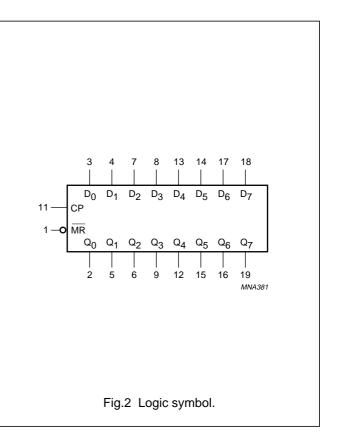
ORDERING INFORMATION

OUTSIDENORTH				PACKAGE		
AMERICA	NORTH AMERICA	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE
74HCT7273D	74HCT7273D	–40 to +125 °C	20	SO	plastic	SOT163-1
74HCT7273N	74HCT7273N		20	DIP	plastic	SOT146-1

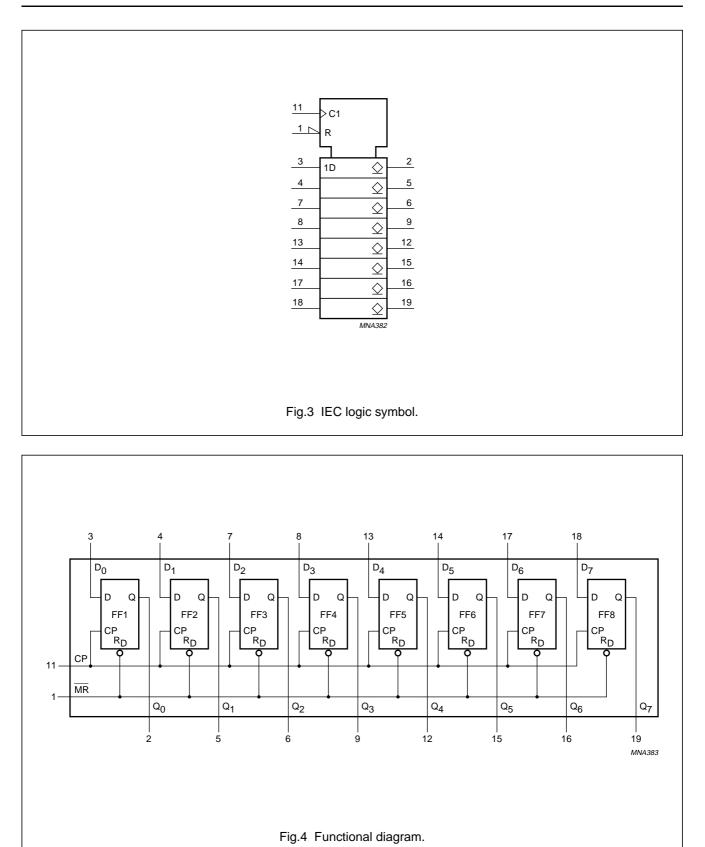
PINNING

PIN	SYMBOL	DESCRIPTION
1	MR	asynchronous master reset (active LOW)
2, 5, 6, 9, 12, 15, 16, 19	Q ₀ to Q ₇	flip-flop outputs
3, 4, 7, 8, 13, 14, 17, 18	D ₀ to D ₇	data inputs
10	GND	ground (0 V)
11	СР	clock input (LOW-to-HIGH, edge triggered)
20	V _{CC}	DC supply voltage





Product specification

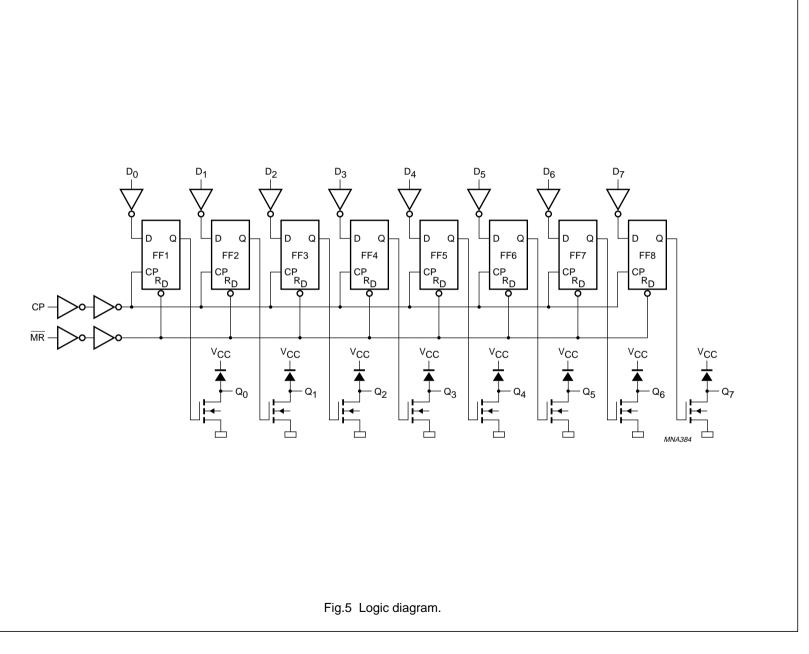


Philips Semiconductors

Product specification

74HCT7273

Octal D-type flip-flop with reset; positive edge-trigger; open drain outputs



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74HCT7273

RECOMMENDED OPERATING CONDITIONS

SYMBOL	DADAMETED	CONDITIONS				
STWBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT
V _{CC}	DC supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	operating ambient	see DC and AC characteristics	-40	-	+85	°C
	temperature	per device	-40	-	+125	°C
$t_r, t_f (\Delta t / \Delta f)$	input rise and fall times	V _{CC} = 2.0 V	-	6.0	500	ns/V
	except for Schmitt-trigger	$V_{CC} = 4.5 V$	-	6.0	500	
	inputs	V _{CC} = 6.0 V	_	6.0	500	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	DC supply voltage		-0.5	+7.0	V
Vo	output voltage		-0.5	+7.0	V
I _{IK}	DC input diode current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC} + 0.5$ V	-	20	mA
I _{OK}	DC output diode current	$V_{\rm O}$ < -0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
lo	DC output source or sink current	$-0.5V < V_O < V_{CC} + 0.5 V$	-	25	mA
I _{CC}	DC V _{CC} or GND current		-	±50	mA
T _{stg}	storage temperature		-65	+150	°C
PD	power dissipation per package	for temperature range: -40 to +125 °C			
	plastic DIP	note 1	-	750	mW
	plastic mini-pack (SO)	note 2	-	500	mW

Note

- 1. For DIP package: above 70 °C the value of P_D derates linearly with 12 mW/K.
- 2. For SO package: above 70 $^\circ\text{C}$ the value of P_D derates linearly with 8 mW/K.

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DC CHARACTERISTICS

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDI	TEST CONDITIONS		T _{amb} (°C)						
SYMBOL	PARAMETER				25		- 40 t	to +85	-40 to +125		UNIT
		OTHER	V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	1.6	-	2.0	_	2.0	-	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	-	1.2	0.8	-	0.8	-	0.8	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 20 \ \mu\text{A}$	4.5	-	0	0.1	-	0.1	-	0.1	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 4.0 \text{ mA}$	4.5	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_{I} = V_{IH} \text{ or } V_{IL}$	5.5	-	-	0.1	-	1.0	-	1.0	μA
I _{OZ}	HIGH level output leakage current	$V_{I} = V_{IL};$ $V_{O} = V_{CC} \text{ or GND}$	4.5 to 5.5	-	_	±0.5	_	±5.0	_	±10.0	μA
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	-	-	8.0	-	80	-	160	μA
Δl _{CC}	additional quiescent supply current per input pin	$V_{I} = V_{CC} - 2.1 V$ other inputs at V_{CC} or GND; $I_{O} = 0$; note 1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

Note

1. The value off additional quiescent supply current (ΔI_{CC}) for a unit load of 1 is given in the specifications. To determine ΔI_{CC} per input, multiply this value by the unit load coefficient shown in Table 1.

Table 1

INPUT	UNIT LOAD COEFFICIENT
MR	1.50
CP	1.50
D _n	0.40

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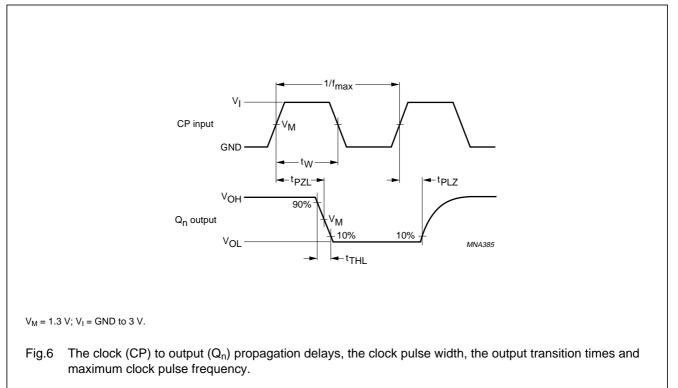
AC CHARACTERISTICS

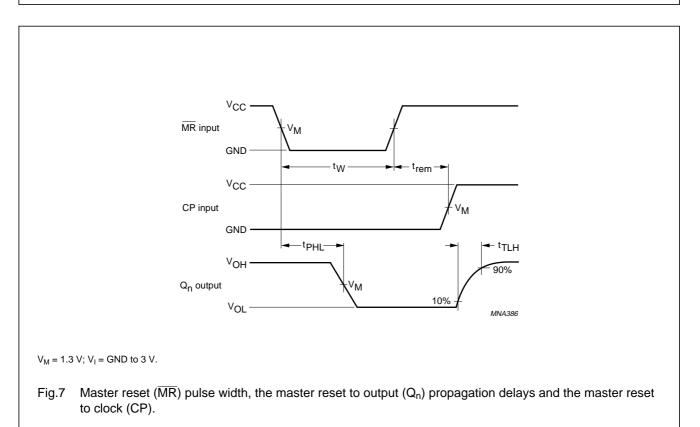
Ground = 0 V; $t_r = t_f \le 6.0 \text{ ns}$; $C_L = 50 \text{ pF}$.

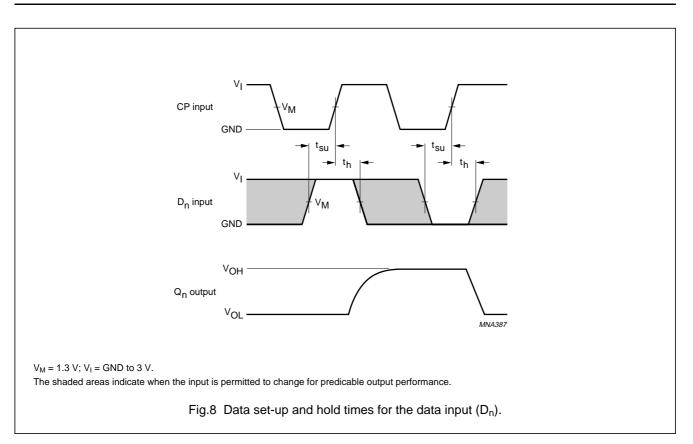
		TEST CONDIT	T _{amb} (°C)								
SYMBOL	PARAMETER	WAVEFORMS	V 00		25		-40	to +85	-40 t	o +125	
		WAVEFORINS	V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
t _{PZL} /t _{PLZ}	propagation delay CP to Q _n	see Figs 6 and 9	4.5	_	16	30	-	38	-	45	ns
t _{PZL}	propagation delay $\overline{\text{MR}}$ to Q_{n}	see Figs 6 and 9	4.5	-	23	34	-	43	-	51	ns
t _{THL}	output transition time	see Figs 6 and 9	4.5	_	7	15	-	19	-	22	ns
t _{TLH}	output transition time	see Figs 7 and 9	4.5	_	-	110	-	110	-	110	ns
t _W	clock pulse width HIGH or LOW	see Figs 6 and 9	4.5	16	9	-	20	-	24	-	ns
t _W	master reset pulse width; LOW	see Figs 7 and 9	4.5	16	8	-	20	-	24	-	ns
t _{rem}	removal time MR to CP	see Figs 7 and 9	4.5	10	-2	-	13	-	15	-	ns
t _{su}	set-up time D _n to CP	see Figs 8 and 9	4.5	12	5	-	15	-	18	-	ns
t _h	hold time D _n to CP	see Figs 8 and 9	4.5	3	-4	-	3	-	3	-	ns
f _{max}	maximum clock pulse frequency	see Figs 6 and 9	4.5	30	56	-	24	-	20	-	MHz

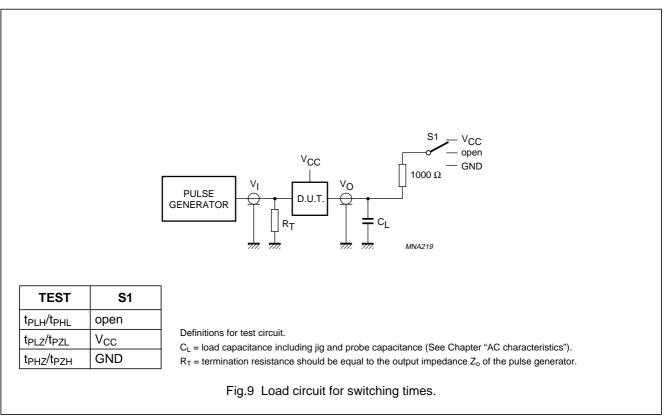
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AC WAVEFORMS

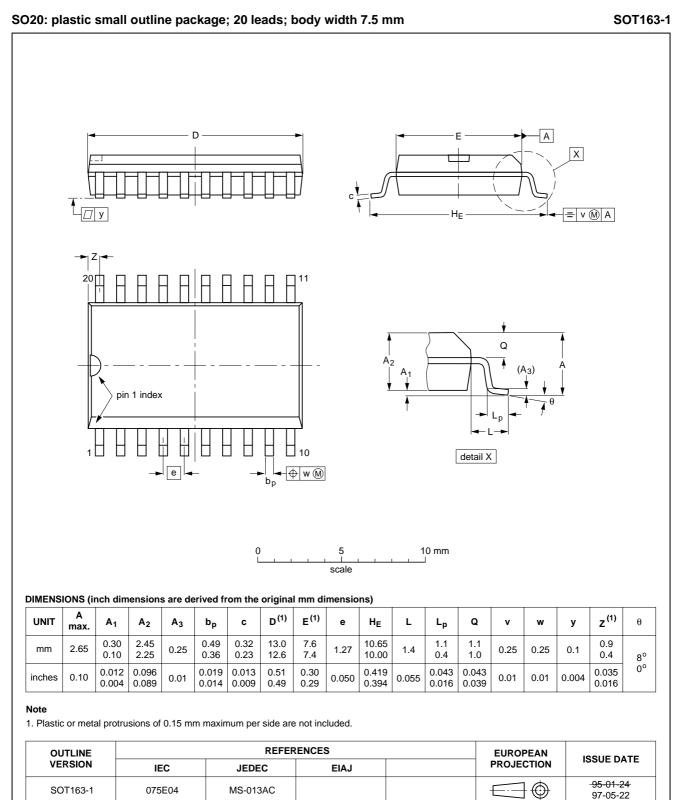






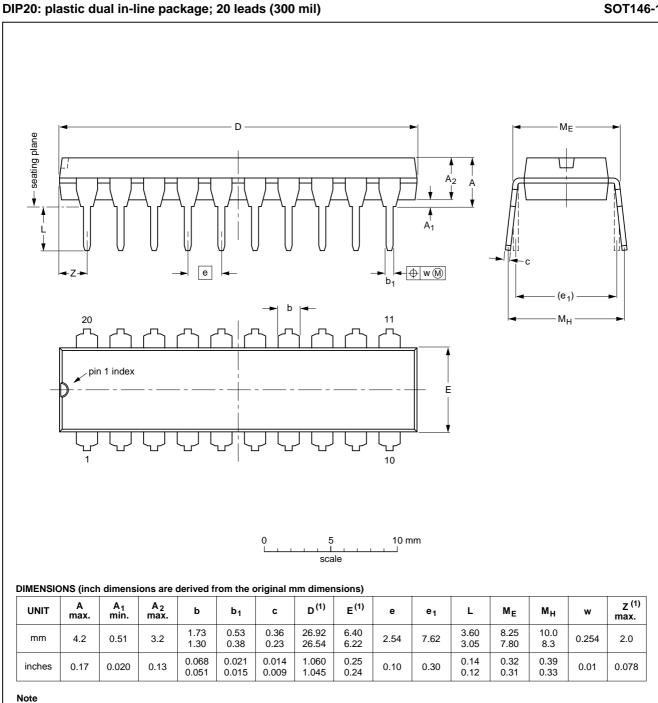


PACKAGE OUTLINES



74HCT7273

Product specification



1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFERENCES		EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT146-1			SC603		-92-11-17 95-05-24

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SOT146-1

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^\circ\text{C}.$

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Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD				
PACKAGE	WAVE	REFLOW ⁽¹⁾			
BGA, SQFP	not suitable	suitable			
HLQFP, HSQFP, HSOP, SMS	not suitable ⁽²⁾	suitable			
PLCC ⁽³⁾ , SO, SOJ	suitable	suitable			
LQFP, QFP, TQFP	not recommended ⁽³⁾⁽⁴⁾	suitable			
SSOP, TSSOP, VSO	not recommended ⁽⁵⁾	suitable			

Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

Introduction to soldering through-hole mount packages

This text gives a brief insight to wave, dip and manual soldering. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (document order number 9398 652 90011).

Wave soldering is the preferred method for mounting of through-hole mount IC packages on a printed-circuit board.

Soldering by dipping or by solder wave

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joints for more than 5 seconds.

The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ($T_{stg(max)}$). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

Manual soldering

Apply the soldering iron (24 V or less) to the lead(s) of the package, either below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

Suitability of through-hole mount IC packages for dipping and wave soldering methods

PACKAGE	SOLDERING METHOD				
FACKAGE	DIPPING	WAVE			
DBS, DIP, HDIP, SDIP, SIL	suitable	suitable ⁽¹⁾			

Note

1. For SDIP packages, the longitudinal axis must be parallel to the transport direction of the printed-circuit board.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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